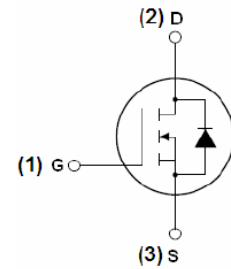


## FEATURES

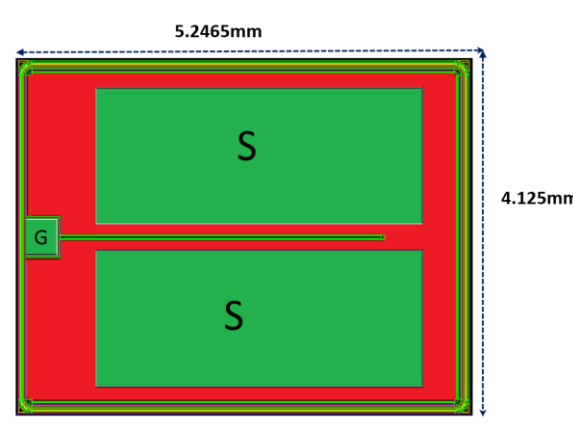
- 100V、57A\* , N-channel
- $R_{DS(on)}=20m\Omega(MAX)$
- Ultra low  $Q_{gd}$
- Fast switching



## Electrical Characteristics(T<sub>J</sub>=25°C)

Parameter	Description	Min.	Typ.	Max.	Unit	Test Condition
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	100			V	$V_{GS}=0V, I_D=250\mu A$
$R_{DS(on)1}$	Static Drain-Source On-Resistance		—	20	m $\Omega$	$V_{GS}=10V, I_D=23.5A$
$V_{GS(th)}$	Gate Threshold Voltage	2.0		4.0	V	$V_{DS}=V_{GS}, I_D=250\mu A$
$I_{DSS}$	Drain-to-Source Leakage Current			1	$\mu A$	$V_{DS}=100V, V_{GS}=0V, T_J=25^\circ C$
$I_{GSS}$	Gate-Body Leakage Current			$\pm 100$	nA	$V_{GS}=\pm 20V$
$V_{SD}$	Body Diode Voltage			1.5	V	$V_{GS}=0V, I_{SD}=57A$
$T_J, T_{stg}$	Operating and Storage Temperature Range	-55~+150			°C	

## Mechanical Date

Die Size	5246.5×4125	$\mu m^2$	
Gate Pad Size	330×420		
Source Pad Size	3700*1500×2		
Scribe Line Size	60	$\mu m$	
Wafer Diameter	150	mm	
Wafer Thickness	280	$\mu m$	
Passivation Frontside	SIN	---	
Source Metallization	AL	4.0	
Drain Metallization	Ti- Ni - Ag	1.3	
Reject Ink Dot Size	0.51	mm	
Recommended Storage Environment	Store in original container, in dessicated nitrogen, with no contamination		

\* Electrical characteristics are reported for the reference packaged part (TO-220/3P/247) and can not be guaranteed in die sales form.

Variations in customer packaging materials, dimensions and processes may affect parametric performance.